



**INTEGRATED CIRCUITS, SILICON MONOLITHIC, CMOS
QUAD LOW TO HIGH VOLTAGE LEVEL SHIFTER WITH
3-STATE OUTPUTS**

BASED ON TYPE 40109B

ESCC Detail Specification No. 9407/003

Issue 4	November 2014
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DCR No.	CHANGE DESCRIPTION
882	Specification upissued to incorporate editorial changes per DCR.

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1 GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 9000
- (b) MIL-STD-883, Test Methods and Procedures for Microelectronics

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 940700301

- Detail Specification Reference: 9407003
- Component Type Variant Number: 01 (as required)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Terminal Material and/or Finish	Weight max g
01	40109B	FP	G2	0.7
02	40109B	FP	G4	0.7
07	40109B	CCP	2	0.6
08	40109B	DIP	G2	2.2
09	40109B	DIP	G4	2.2
10	40109B	SO	G2	0.7
11	40109B	SO	G4	0.7

The terminal material and/or finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Units	Remarks
Supply Voltage	V_{CC}, V_{DD}	-0.5 to 18	V	Note 1
Input Voltage	V_{IN}	-0.5 to 18.5	V	Note 1 Power on
Input Current	I_{IN}	± 10	mA	Note 2
Device Power Dissipation (Continuous)	P_D	200	mW	-
Power Dissipation per Output	P_{DSO}	100	mW	-
Operating Temperature Range	T_{op}	-55 to +125	$^{\circ}C$	T_{amb}
Storage Temperature Range	T_{stg}	-65 to +150	$^{\circ}C$	-
Soldering Temperature For FP, DIP and SO For CCP	T_{sol}	+265 +245	$^{\circ}C$	Note 3 Note 4

NOTES:

1. Device is functional for $3V \leq V_{CC} \leq 15V$ and $3V \leq V_{DD} \leq 15V$. V_{IN} may exceed V_{CC} and V_{DD} . V_{CC} may exceed V_{DD} .
2. For any single input.
3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same terminal shall not be resoldered until 3 minutes have elapsed.
4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

1.6 HANDLING PRECAUTIONS

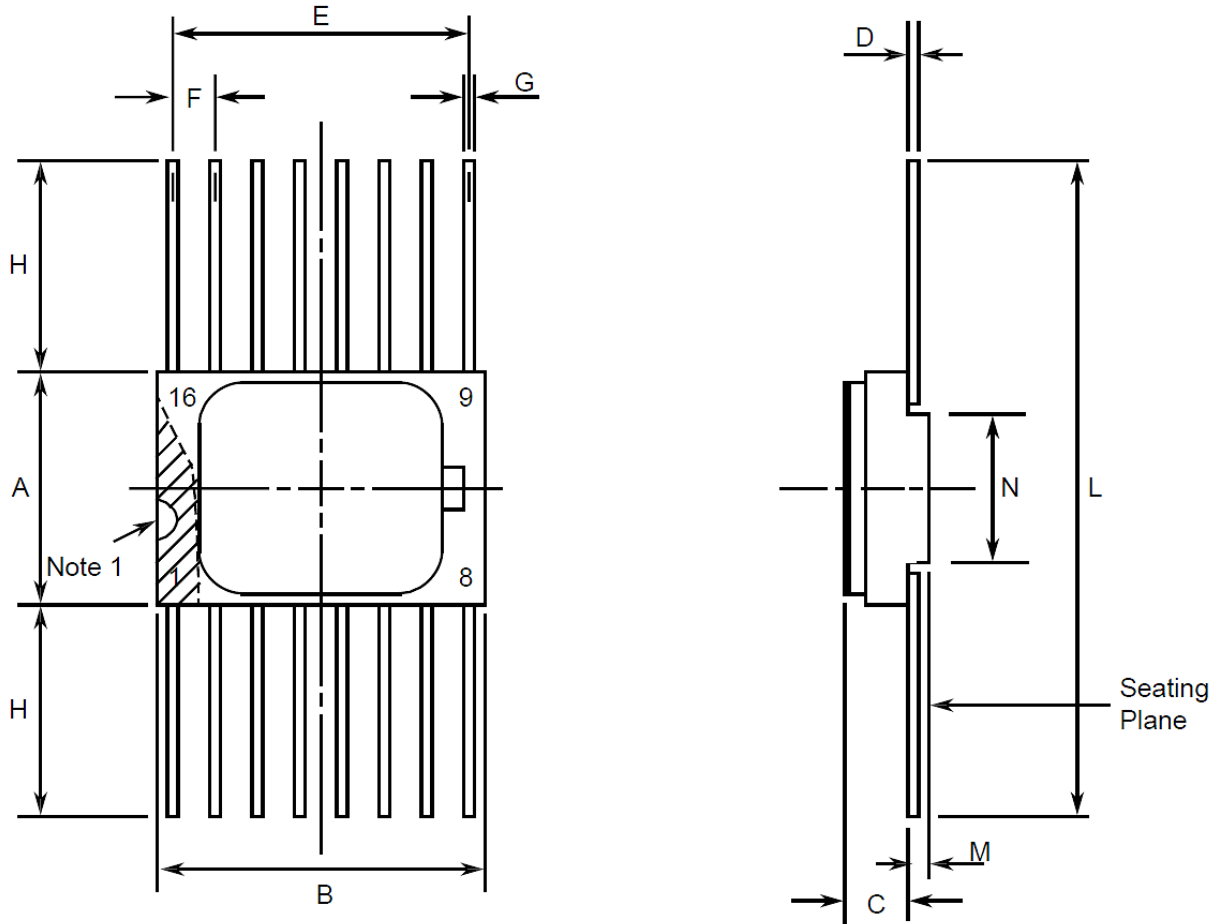
These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are categorised as Class 1 per ESCC Basic Specification No. 23800 with a minimum Critical Path Failure Voltage of 400 Volts.

1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

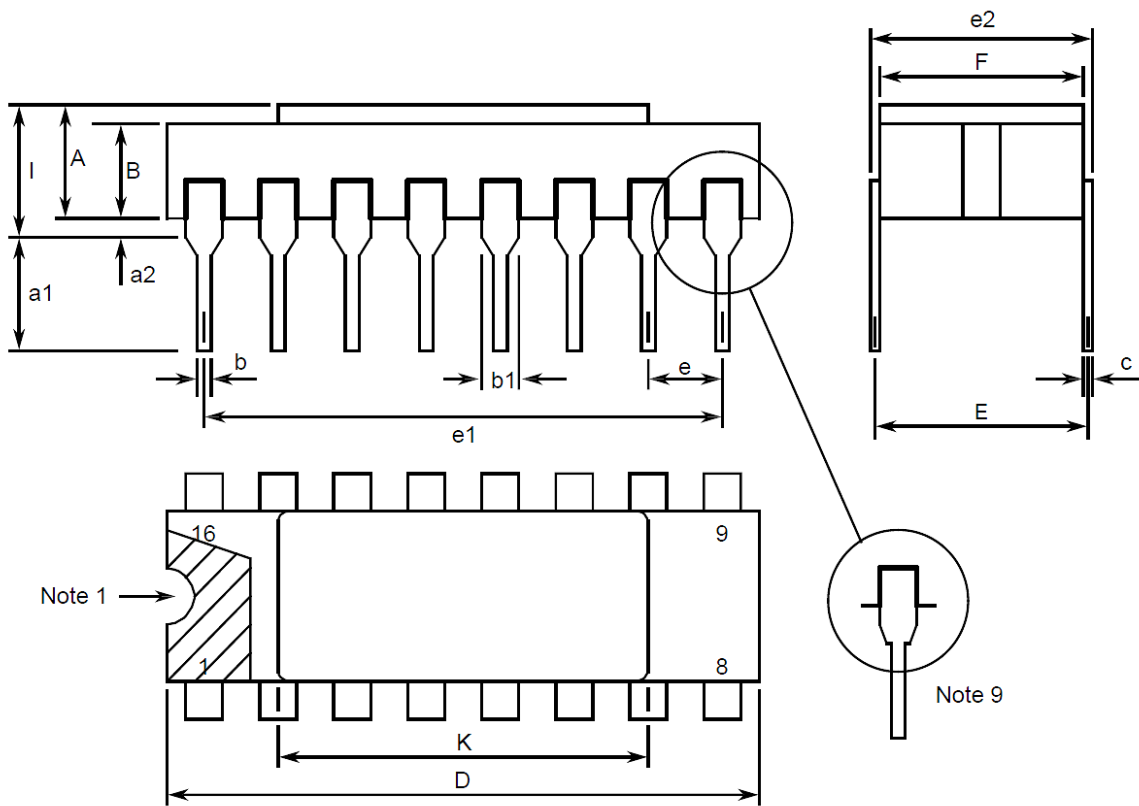
Consolidated Notes are given following the case drawings and dimensions.

1.7.1 Flat Package (FP) - 16 Pin



Symbols	Dimensions mm		Notes
	Min	Max	
A	6.75	7.06	
B	9.76	10.14	
C	1.49	1.95	
D	0.1	0.15	5
E	8.76	9.01	
F	1.27 BSC		3, 6
G	0.38	0.48	5
H	6	-	5
L	18.75	22	
M	0.33	0.43	
N	4.32 TYPICAL		

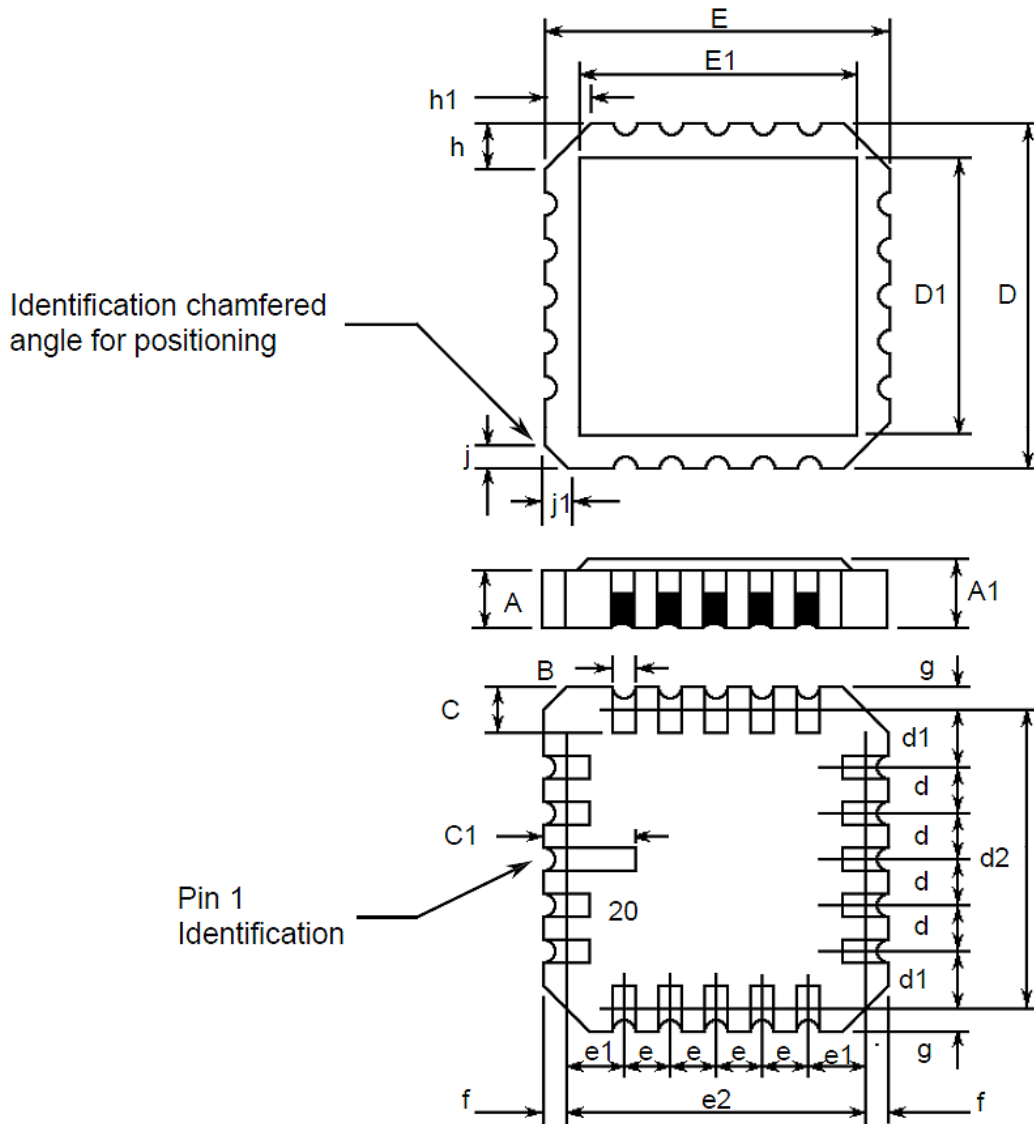
1.7.2 Dual-in-line Package (DIP) - 16 Pin



Symbols	Dimensions mm		Notes
	Min	Max	
A	2.1	2.71	
a1	3	3.7	
a2	0.63	1.14	2
B	1.82	2.39	
b	0.4	0.5	5
b1	1.14	1.5	5
c	0.2	0.3	5
D	20.06	20.58	
E	7.36	7.87	
e	2.54 BSC		4, 6
e1	17.65	17.9	
e2	7.62	8.12	
F	7.29	7.7	
I	-	3.83	

Symbols	Dimensions mm		Notes
	Min	Max	
K	10.9	12.1	

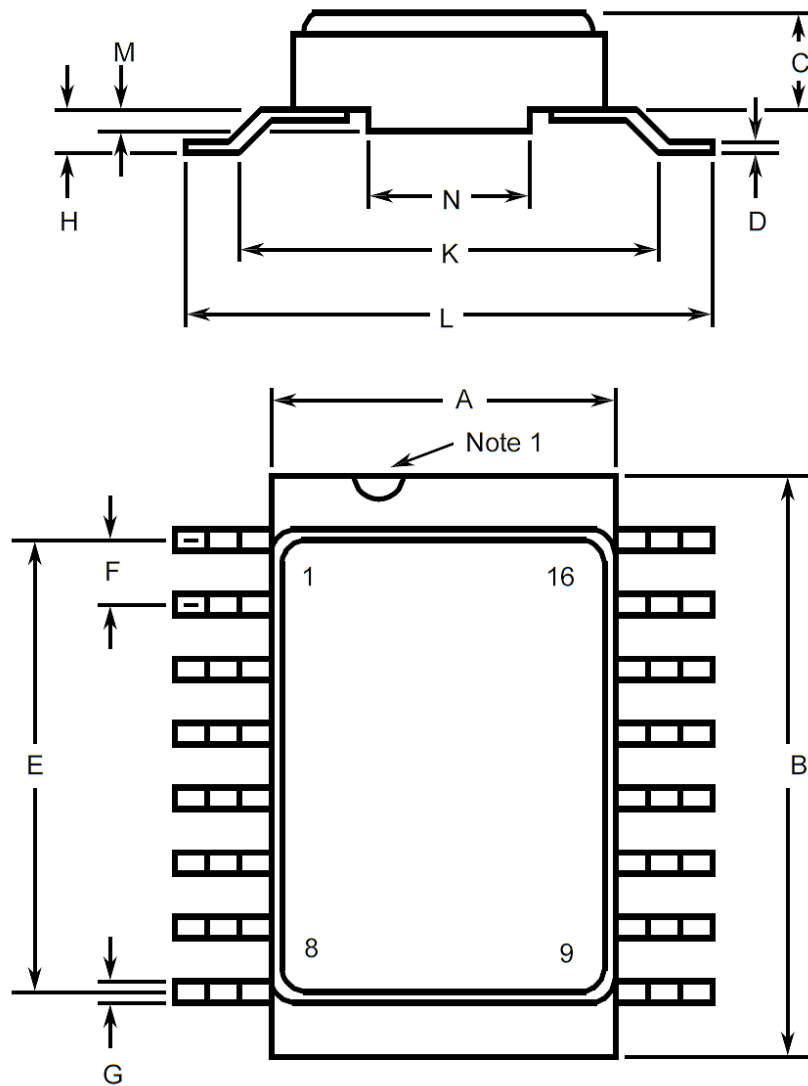
1.7.3 Chip Carrier Package (CCP) - 20 Terminal



Symbols	Dimensions mm		Notes
	Min	Max	
A	1.14	1.95	
A1	1.63	2.36	
B	0.55	0.72	5
C	1.06	1.47	5

Symbols	Dimensions mm		Notes
	Min	Max	
C1	1.91	2.41	
D	8.67	9.09	
D1	7.21	7.52	
d, d1	1.27 BSC		3
d2	7.62 BSC		
E	8.67	9.09	
E1	7.21	7.52	
e, e1	1.27 BSC		3
e2	7.62 BSC		
f, g	-	0.76	
h, h1	1.01 TYPICAL		8
j, j1	0.51 TYPICAL		7

1.7.4 Small Outline Ceramic Package (SO) - 16 Pin



Symbols	Dimensions mm		Notes
	Min	Max	
A	6.75	7.06	
B	9.76	10.14	
C	1.49	1.95	
D	0.1	0.15	5
E	8.76	9.01	
F	1.27 BSC		3, 6
G	0.38	0.48	5
H	0.6	0.9	5

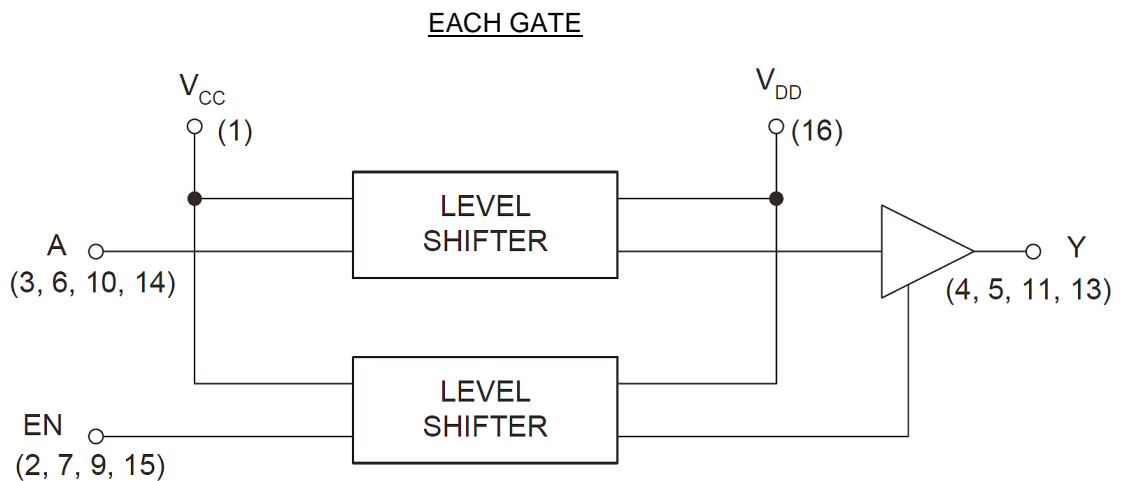
Symbols	Dimensions mm		Notes
	Min	Max	
K	9 TYPICAL		
L	10	10.65	
M	0.33	0.43	
N	4.31 TYPICAL		

1.7.5 Notes to Physical Dimensions and Terminal Identification

1. Index area; a notch or a dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages, the index shall be as shown.
2. The dimension shall be measured from the seating plane to the base plane.
3. The true position pin spacing is 1.27mm between centrelines. Each pin centreline shall be located within $\pm 0.13\text{mm}$ of its true longitudinal position relative to Pin 1 and the highest pin number.
4. The true position pin spacing is 2.54mm between centrelines. Each pin centreline shall be located within $\pm 0.25\text{mm}$ of its true longitudinal position relative to Pin 1 and the highest pin number.
5. All terminals.
6. 14 spaces.
7. Index corner only - 2 dimensions.
8. 3 non-index corners - 6 dimensions.
9. For all pins, either pin shape may be supplied.

1.8 FUNCTIONAL DIAGRAM

Pin numbers relate to FP, DIP and SO packages only.



1.9 PIN ASSIGNMENT

Pin	Function		Pin	Function	
	FP, DIP and SO	CCP		FP, DIP and SO	CCP
1	V _{CC} (Supply Voltage Input Side)	V _{CC} (Supply Voltage Input Side)	11	3Y Output	3EN Input (Enable)
2	1EN Input (Enable)	1EN Input (Enable)	12	-	3A Input
3	1A Input	-	13	4Y Output	-
4	1Y Output	1A Input	14	4A Input	3Y Output
5	2Y Output	1Y Output	15	4EN Input (Enable)	-
6	2A Input	2Y Output	16	V _{DD} (Supply Voltage Output Side)	4Y Output
7	2EN Input (Enable)	2A Input	17	-	4A Input
8	V _{SS}	-	18	-	-
9	3EN Input (Enable)	2EN Input (Enable)	19	-	4EN Input (Enable)
10	3A Input	V _{SS}	20	-	V _{DD} (Supply Voltage Output Side)

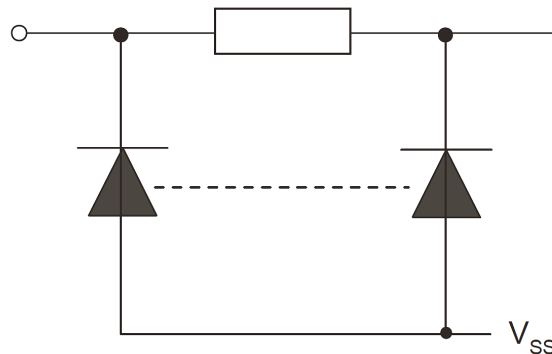
1.10 TRUTH TABLE

- Logic Level Definitions: L = Low Level, H = High Level based on V_{CC} at Inputs and V_{DD} at Outputs, X = Irrelevant, Z = High Impedance.

EACH GATE

INPUTS		OUTPUT
A	EN	Y
L	H	L
H	H	H
X	L	Z

1.11 INPUT PROTECTION NETWORK



2 REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

None.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) Terminal identification.
- (b) The ESCC qualified components symbol (for ESCC qualified components only).
- (c) The ESCC Component Number.
- (d) Traceability information.

2.3 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures. Consolidated Notes are given after the tables.

2.3.1 Room Temperature Electrical Measurements

The measurements shall be performed at $T_{amb} = +22 \pm 3 \text{ }^\circ\text{C}$.

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Functional Test 1	-	3014	Verify Truth Table without Load $V_{IL} = 0V, V_{IH} = 3V$ $V_{CC} = V_{DD} = 3V, V_{SS} = 0V$ Note 2	-	-	-
Functional Test 2	-	3014	Verify Truth Table without Load $V_{IL} = 0V, V_{IH} = 15V$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$ Note 2	-	-	-
Quiescent Current	I_{DD}	3005	$V_{IL} = 0V, V_{IH} = 15V$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$ Note 3	-	500	nA
Low Level Input Current	I_{IL}	3009	$V_{IN} \text{ (Under Test)} = 0V$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$	-	-50	nA
High Level Input Current	I_{IH}	3010	$V_{IN} \text{ (Under Test)} = 15V$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$	-	50	nA
Low Level Output Voltage 1	V_{OL1}	3007	$V_{IL} = 0V, V_{IH} = 15V,$ $I_{OL} = 0A$ $V_{CC} = 5V, V_{DD} = 15V,$ $V_{SS} = 0V$	-	50	mV
Low Level Output Voltage 2 (Noise Immunity)	V_{OL2}	3007	$V_{IL} = 1.5V, V_{IH} = 3.5V,$ $I_{OL} = 0A$ $V_{CC} = V_{DD} = 5V, V_{SS} = 0V$	-	500	mV
Low Level Output Voltage 3 (Noise Immunity)	V_{OL3}	3007	$V_{IL} = 4V, V_{IH} = 11V,$ $I_{OL} = 0A$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$	-	1.5	V
High Level Output Voltage 1	V_{OH1}	3006	$V_{IL} = 0V, V_{IH} = 15V,$ $I_{OH} = 0A$ $V_{CC} = 5V, V_{DD} = 15V,$ $V_{SS} = 0V$	14.95	-	V

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
High Level Output Voltage 2 (Noise Immunity)	V_{OH2}	3006	$V_{IL} = 1.5V, V_{IH} = 3.5V,$ $I_{OH} = 0A$ $V_{CC} = V_{DD} = 5V, V_{SS} = 0V$	4.5	-	V
High Level Output Voltage 3 (Noise Immunity)	V_{OH3}	3006	$V_{IL} = 4V, V_{IH} = 11V,$ $I_{OH} = 0A$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$	13.5	-	V
Low Level Output Current 1	I_{OL1}	-	$V_{IL} = 0V, V_{IH} = 5V,$ $V_{OL} = 0.4V$ $V_{CC} = V_{DD} = 5V, V_{SS} = 0V$ Note 4	510	-	μA
Low Level Output Current 2	I_{OL2}	-	$V_{IL} = 0V, V_{IH} = 15V,$ $V_{OL} = 1.5V$ $V_{CC} = 5V, V_{DD} = 15V,$ $V_{SS} = 0V$ Note 4	3.4	-	mA
High Level Output Current 1	I_{OH1}	-	$V_{IL} = 0V, V_{IH} = 5V,$ $V_{OH} = 4.6V$ $V_{CC} = V_{DD} = 5V, V_{SS} = 0V$ Note 4	-510	-	μA
High Level Output Current 2	I_{OH2}	-	$V_{IL} = 0V, V_{IH} = 15V,$ $V_{OH} = 13.5V$ $V_{CC} = 5V, V_{DD} = 15V,$ $V_{SS} = 0V$ Note 4	-3.4	-	mA
Threshold Voltage N-Channel	V_{THN}	-	1A Input at Ground All Other Inputs: $V_{IN} = 5V$ $V_{CC} = 5V, V_{DD} = 12V,$ $I_{SS} = -10\mu A$	-0.7	-3	V
Threshold Voltage P-Channel	V_{THP}	-	1A Input at Ground All Other Inputs: $V_{IN} = -5V$ $V_{DD} = 7V, V_{SS} = -5V,$ $I_{CC} = 10\mu A$	0.7	3	V
Output Leakage Current Third State, Low Level Applied	I_{OZL}	3020	$V_{IL} = 0V$ $V_{IH} = 18V$ $V_{OL} = 0V$ $V_{CC} = 5V, V_{DD} = 18V,$ $V_{SS} = 0V$	-	-400	nA

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Output Leakage Current Third State, High Level Applied	I_{OZH}	3021	$V_{IL} = 0V$ $V_{IH} = 18V$ $V_{OH} = 15V$ $V_{CC} = 5V, V_{DD} = 18V, V_{SS} = 0V$	-	400	nA
Input Clamp Voltage, to V_{SS}	V_{IC}	-	I_{IN} (Under Test) = $-100\mu A$ $V_{CC} = 0V, V_{DD} = \text{Open}, V_{SS} = 0V$ All Other Pins Open	-	-2	V
Input Capacitance	C_{IN}	3012	V_{IN} (Not Under Test) = $0V$ $V_{CC} = V_{DD} = V_{SS} = 0V$ $f = 100kHz$ to $1MHz$ Note 5	-	10	pF
Propagation Delay Low to High 1, 1A to 1Y 2A to 2Y 3A to 3Y 4A to 4Y (Low to High Level Shift)	t_{PLH1}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 5V,$ $V_{CC} = 5V, V_{DD} = 10V,$ $V_{SS} = 0V$ Note 6	-	260	ns
Propagation Delay High to Low 1, 1A to 1Y 2A to 2Y 3A to 3Y 4A to 4Y (Low to High Level Shift)	t_{PHL1}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 5V,$ $V_{CC} = 5V, V_{DD} = 10V,$ $V_{SS} = 0V$ Note 6	-	600	ns
Propagation Delay Low to High 2, 1A to 1Y 2A to 2Y 3A to 3Y 4A to 4Y (High to Low Level Shift)	t_{PLH2}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 10V,$ $V_{CC} = 10V, V_{DD} = 5V,$ $V_{SS} = 0V$ Note 6	-	460	ns

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Propagation Delay High to Low 2, 1A to 1Y 2A to 2Y 3A to 3Y 4A to 4Y (High to Low Level Shift)	t_{PHL2}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 10V,$ $V_{CC} = 10V, V_{DD} = 5V,$ $V_{SS} = 0V$ Note 6	-	1.6	ms
Output Enable Time High Impedance to Low Output 1, 1EN to 1Y 2EN to 2Y 3EN to 3Y 4EN to 4Y (Low to High Level Shift)	t_{PZL1}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 5V,$ $V_{CC} = 5V, V_{DD} = 10V,$ $V_{SS} = 0V$ Note 6	-	200	ns
Output Disable Time Low Output to High Impedance 1, 1EN to 1Y 2EN to 2Y 3EN to 3Y 4EN to 4Y (Low to High Level Shift)	t_{PLZ1}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 5V,$ $V_{CC} = 5V, V_{DD} = 10V,$ $V_{SS} = 0V$ Note 6	-	740	ns
Output Enable Time High Impedance to Low Output 2, 1EN to 1Y 2EN to 2Y 3EN to 3Y 4EN to 4Y (High to Low Level Shift)	t_{PZL2}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 10V,$ $V_{CC} = 10V, V_{DD} = 5V,$ $V_{SS} = 0V$ Note 6	-	240	ns
Output Disable Time Low Output to High Impedance 2, 1EN to 1Y 2EN to 2Y 3EN to 3Y 4EN to 4Y (High to Low Level Shift)	t_{PLZ2}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 10V,$ $V_{CC} = 10V, V_{DD} = 5V,$ $V_{SS} = 0V$ Note 6	-	1.6	ms

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Output Enable Time High Impedance to High Output 1, 1EN to 1Y 2EN to 2Y 3EN to 3Y 4EN to 4Y (Low to High Level Shift)	t_{PZH1}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 5V,$ $V_{CC} = 5V, V_{DD} = 10V,$ $V_{SS} = 0V$ Note 6	-	640	ns
Output Disable Time High Output to High Impedance 1, 1EN to 1Y 2EN to 2Y 3EN to 3Y 4EN to 4Y (Low to High Level Shift)	t_{PHZ1}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 5V,$ $V_{CC} = 5V, V_{DD} = 10V,$ $V_{SS} = 0V$ Note 6	-	120	ns
Output Enable Time High Impedance to High Output 2, 1EN to 1Y 2EN to 2Y 3EN to 3Y 4EN to 4Y (High to Low Level Shift)	t_{PZH2}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 10V,$ $V_{CC} = 10V, V_{DD} = 5V,$ $V_{SS} = 0V$ Note 6	-	1.5	ms
Output Disable Time High Output to High Impedance 2, 1EN to 1Y 2EN to 2Y 3EN to 3Y 4EN to 4Y (High to Low Level Shift)	t_{PHZ2}	3003	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 10V,$ $V_{CC} = 10V, V_{DD} = 5V,$ $V_{SS} = 0V$ Note 6	-	240	ns
Transition Time Low to High 1, 1Y, 2Y, 3Y, 4Y (Low to High Level Shift)	t_{TLH1}	3004	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 5V,$ $V_{CC} = 5V, V_{DD} = 10V,$ $V_{SS} = 0V$ Note 6	-	100	ns

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Transition Time High to Low 1, 1Y, 2Y, 3Y, 4Y (Low to High Level Shift)	t_{THL1}	3004	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 5V,$ $V_{CC} = 5V, V_{DD} = 10V,$ $V_{SS} = 0V$ Note 6	-	100	ns
Transition Time Low to High 2, 1Y, 2Y, 3Y, 4Y (High to Low Level Shift)	t_{TLH2}	3004	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 10V,$ $V_{CC} = 10V, V_{DD} = 5V,$ $V_{SS} = 0V$ Note 6	-	200	ns
Transition Time High to Low 2, 1Y, 2Y, 3Y, 4Y (High to Low Level Shift)	t_{THL2}	3004	V_{IN} (Under Test) = Pulse Generator V_{IN} (Remaining Inputs) = Truth Table $V_{IL} = 0V, V_{IH} = 10V,$ $V_{CC} = 10V, V_{DD} = 5V,$ $V_{SS} = 0V$ Note 6	-	200	ns

2.3.2 High and Low Temperatures Electrical Measurements

The measurements shall be performed at $T_{amb} = +125 (+0 -5) ^\circ C$ and $T_{amb} = -55 (+5 -0) ^\circ C$.

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Functional Test 1	-	3014	Verify Truth Table without Load $V_{IL} = 0V, V_{IH} = 3V$ $V_{CC} = V_{DD} = 3V, V_{SS} = 0V$ Note 2	-	-	-
Functional Test 2	-	3014	Verify Truth Table without Load $V_{IL} = 0V, V_{IH} = 15V$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$ Note 2	-	-	-

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Quiescent Current	I_{DD}	3005	$V_{IL} = 0V, V_{IH} = 15V$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$ Note 3 $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	- -	15 0.5	μA
Low Level Input Current	I_{IL}	3009	$V_{IN} \text{ (Under Test)} = 0V$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$ $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	- -	-100 -50	nA
High Level Input Current	I_{IH}	3010	$V_{IN} \text{ (Under Test)} = 15V$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$ $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	- -	100 50	nA
Low Level Output Voltage 1	V_{OL1}	3007	$V_{IL} = 0V, V_{IH} = 15V,$ $I_{OL} = 0A$ $V_{CC} = 5V, V_{DD} = 15V,$ $V_{SS} = 0V$	-	50	mV
Low Level Output Voltage 2 (Noise Immunity)	V_{OL2}	3007	$V_{IL} = 1.5V, V_{IH} = 3.5V,$ $I_{OL} = 0A$ $V_{CC} = V_{DD} = 5V, V_{SS} = 0V$	-	500	mV
Low Level Output Voltage 3 (Noise Immunity)	V_{OL3}	3007	$V_{IL} = 4V, V_{IH} = 11V,$ $I_{OL} = 0A$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$	-	1.5	V
High Level Output Voltage 1	V_{OH1}	3006	$V_{IL} = 0V, V_{IH} = 15V,$ $I_{OH} = 0A$ $V_{CC} = 5V, V_{DD} = 15V,$ $V_{SS} = 0V$	14.95	-	V
High Level Output Voltage 2 (Noise Immunity)	V_{OH2}	3006	$V_{IL} = 1.5V, V_{IH} = 3.5V,$ $I_{OH} = 0A$ $V_{CC} = V_{DD} = 5V, V_{SS} = 0V$	4.5	-	V
High Level Output Voltage 3 (Noise Immunity)	V_{OH3}	3006	$V_{IL} = 4V, V_{IH} = 11V,$ $I_{OH} = 0A$ $V_{CC} = V_{DD} = 15V,$ $V_{SS} = 0V$	13.5	-	V

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Low Level Output Current 1	I_{OL1}	-	$V_{IL} = 0V, V_{IH} = 5V,$ $V_{OL} = 0.4V$ $V_{CC} = V_{DD} = 5V, V_{SS} = 0V$ Note 4 $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	360 640	- -	μA
Low Level Output Current 2	I_{OL2}	-	$V_{IL} = 0V, V_{IH} = 15V,$ $V_{OL} = 1.5V$ $V_{CC} = 5V, V_{DD} = 15V,$ $V_{SS} = 0V$ Note 4 $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	2.4 4.2	- -	mA
High Level Output Current 1	I_{OH1}	-	$V_{IL} = 0V, V_{IH} = 5V,$ $V_{OH} = 4.6V$ $V_{CC} = V_{DD} = 5V, V_{SS} = 0V$ Note 4 $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	-360 -640	- -	μA
High Level Output Current 2	I_{OH2}	-	$V_{IL} = 0V, V_{IH} = 15V,$ $V_{OH} = 13.5V$ $V_{CC} = 5V, V_{DD} = 15V,$ $V_{SS} = 0V$ Note 4 $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	-2.4 -4.2	- -	mA
Threshold Voltage N-Channel	V_{THN}	-	1A Input at Ground All Other Inputs: $V_{IN} = 5V$ $V_{CC} = 5V, V_{DD} = 12V,$ $I_{SS} = -10\mu A$ $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	-0.3 -0.7	-3.5 -3.5	V
Threshold Voltage P-Channel	V_{THP}	-	1A Input at Ground All Other Inputs: $V_{IN} = -5V$ $V_{DD} = 7V, V_{SS} = -5V,$ $I_{CC} = 10\mu A$ $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	0.3 0.7	3.5 3.5	V

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions Note 1	Limits		Units
				Min	Max	
Output Leakage Current Third State, Low Level Applied	I_{OZL}	3020	$V_{IL} = 0V$ $V_{IH} = 18V$ $V_{OL} = 0V$ $V_{CC} = 5V, V_{DD} = 18V,$ $V_{SS} = 0V$ $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	- -	-12 -0.4	μA
Output Leakage Current Third State, High Level Applied	I_{OZH}	3021	$V_{IL} = 0V$ $V_{IH} = 18V$ $V_{OH} = 15V$ $V_{CC} = 5V, V_{DD} = 18V,$ $V_{SS} = 0V$ $T_{amb} = +125\text{ }^{\circ}C$ $T_{amb} = -55\text{ }^{\circ}C$	- -	12 0.4	μA

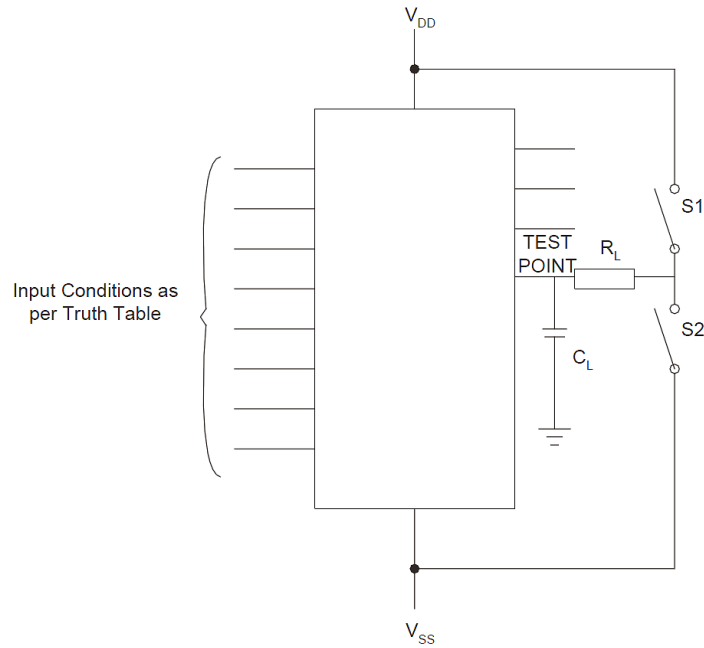
2.3.3 Notes to Electrical Measurement Tables

1. Unless otherwise specified all inputs and outputs shall be tested for each characteristic, inputs not under test shall be $V_{IN} = V_{SS}$ or V_{DD} and outputs not under test shall be open.
2. Functional tests shall be performed to verify Truth Table with $V_{OH} \geq V_{DD}-0.5V, V_{OL} \leq 0.5V$. The maximum time to output comparator strobe = 300 μs .
3. Quiescent Current shall be tested using the following input conditions:
 - (a) Inputs 1A = 2A = 3A = 4A = V_{IL}
 - (b) Inputs 1A = 2A = 3A = 4A = V_{IH}
4. Interchange of forcing and measuring parameters is permitted.
5. Guaranteed but not tested.
6. Read and record measurements shall be performed on a sample of 32 components with 0 failures permitted.

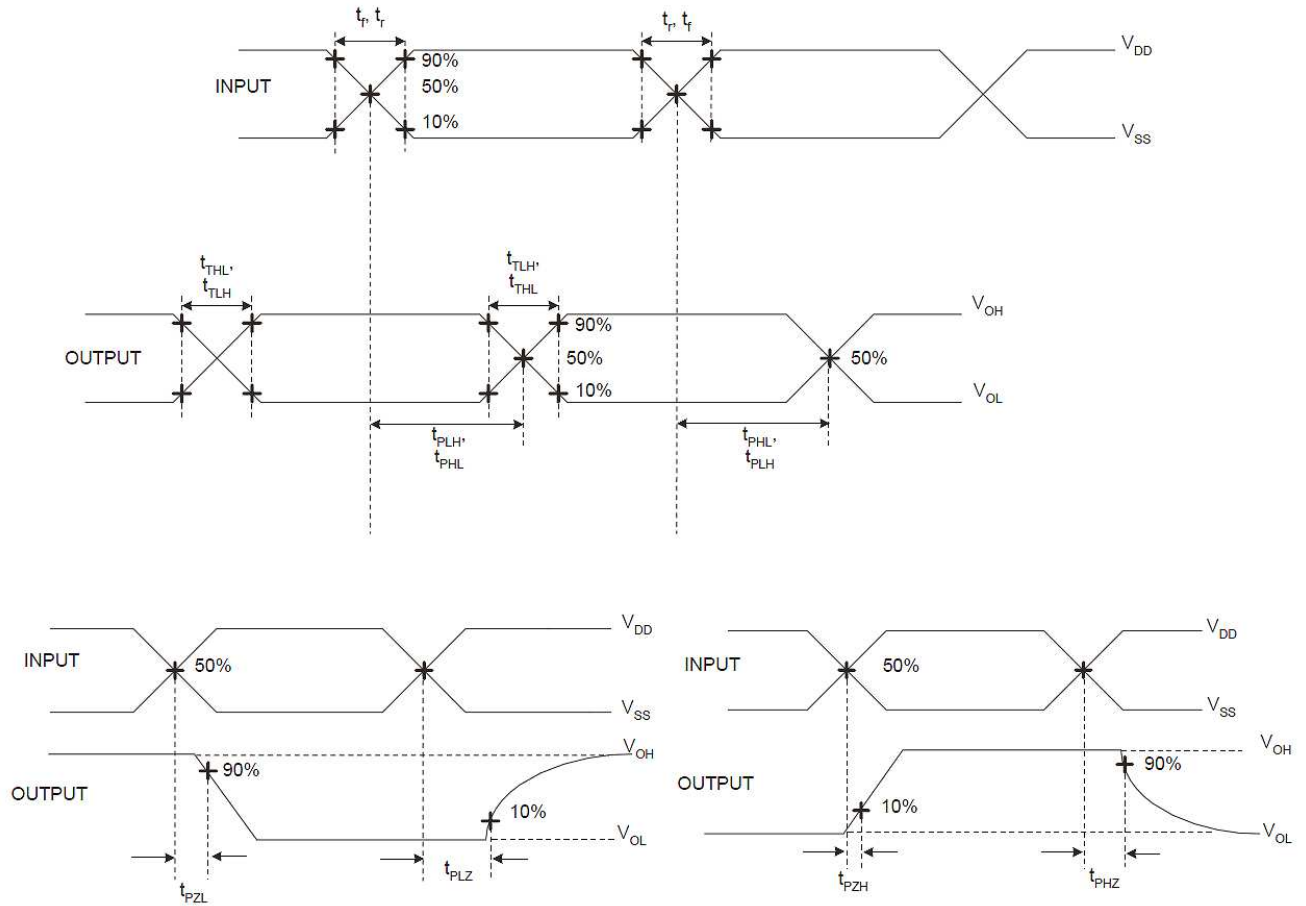
The pulse generator shall have the following characteristics:

$V_{GEN} = 0$ to V_{CC} ; $f_{GEN} = 500kHz$; t_r and $t_f \leq 15ns$ (10% to 90%); duty cycle = 50%; $Z_{out} = 50\Omega$. Output load capacitance $C_L = 50pF \pm 5\%$ including scope probe, wiring and stray capacitance without component in the test fixture, and output load resistance $R_L = 1k\Omega \pm 5\%$.

Propagation delay and transition time shall be measured as follows:



Parameter	R_L	S1	S2
t_{PZH}	1k Ω	Open	Closed
t_{PZL}		Closed	Open
t_{PHZ}		Open	Closed
t_{PLZ}		Closed	Open
$t_{PHL}, t_{PLH}, t_{THL}, t_{TLH}$	200k Ω	Open	Closed



2.4 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3 \text{ }^\circ\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Quiescent Current	I_{DD}	± 75	-	500	nA
Low Level Output Current 1	I_{OL1}	$\pm 15\%$ (2)	510	-	μA
High Level Output Current 1	I_{OH1}	$\pm 15\%$ (2)	-510	-	μA

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Output Leakage Current Third State, Low Level Applied	I_{OZL}	± 60	-	-400	nA
Output Leakage Current Third State, High Level Applied	I_{OZH}	± 60	-	400	nA
Threshold Voltage N-Channel	V_{THN}	± 0.3	-0.7	-3	V
Threshold Voltage P-Channel	V_{THP}	± 0.3	0.7	3	V

NOTES:

1. Unless otherwise specified all inputs and outputs shall be tested for each characteristic.
2. Percentage of limit value if voltage is the measuring parameter.

2.5 **INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS**

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +22 \pm 3 \text{ }^\circ\text{C}$.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic where specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Functional Test 1	-	-	-	-	-
Quiescent Current	I_{DD}	± 75	-	500	nA
Low Level Input Current	I_{IL}	-	-	-50	nA
High Level Input Current	I_{IH}	-	-	50	nA
Low Level Output Voltage 1	V_{OL1}	-	-	50	mV
Low Level Output Voltage 2 (Noise Immunity)	V_{OL2}	-	-	500	mV
High Level Output Voltage 1	V_{OH1}	-	14.95	-	V

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
High Level Output Voltage 2 (Noise Immunity)	V_{OH2}	-	4.5	-	V
Low Level Output Current 1	I_{OL1}	$\pm 15\%$ (3)	510	-	μA
Low Level Output Current 2	I_{OL2}	$\pm 15\%$ (3)	3.4	-	mA
High Level Output Current 1	I_{OH1}	$\pm 15\%$ (3)	-510	-	μA
High Level Output Current 2	I_{OH2}	$\pm 15\%$ (3)	-3.4	-	mA
Output Leakage Current Third State, Low Level Applied	I_{OZL}	± 60	-	-400	nA
Output Leakage Current Third State, High Level Applied	I_{OZH}	± 60	-	400	nA
Threshold Voltage N-Channel	V_{THN}	± 0.3	-0.7	-3	V
Threshold Voltage P-Channel	V_{THP}	± 0.3	0.7	3	V

NOTES:

1. Unless otherwise specified all inputs and outputs shall be tested for each characteristic.
2. The drift values (Δ) are applicable to the Operating Life test only.
3. Percentage of limit value if voltage is the measuring parameter.

2.6 HIGH TEMPERATURE REVERSE BIAS BURN-IN CONDITIONS

2.6.1 N-Channel HTRB

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+125 (+0 -5)	°C
Outputs Y (All Gates)	V_{OUT}	Open	V
Inputs 1A, 3A, 4A, 1EN	V_{IN}	$V_{DD}/2$	V
Inputs 2A, 2EN, 3EN, 4EN	V_{IN}	V_{SS}	V
Positive Supply Voltage (Input Side)	V_{CC}	$V_{DD}/2$	V
Positive Supply Voltage (Output Side)	V_{DD}	15 (+0 -0.5)	V
Negative Supply Voltage	V_{SS}	0	V
Duration	t	72	Hours

NOTES:

1. Input Protection Resistor = 2kΩ min to 47kΩ max.

2.6.2 P-Channel HTRB

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+125 (+0 -5)	°C
Outputs Y (All Gates)	V_{OUT}	Open	V
Inputs 1A, 3A, 4A, 1EN	V_{IN}	V_{SS}	V
Inputs 2A, 2EN, 3EN, 4EN	V_{IN}	$V_{DD}/2$	V
Positive Supply Voltage (Input Side)	V_{CC}	$V_{DD}/2$	V
Positive Supply Voltage (Output Side)	V_{DD}	15 (+0 -0.5)	V
Negative Supply Voltage	V_{SS}	0	V
Duration	t	72	Hours

NOTES:

1. Input Protection Resistor = 2kΩ min to 47kΩ max.

2.7 POWER BURN-IN CONDITIONS

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+125 (+0 -5)	°C
Outputs Y (All Gates)	V_{OUT}	$V_{DD}/2$	V
Inputs EN (All Gates)	V_{IN}	V_{DD}	V
Inputs A (All Gates)	V_{IN}	V_{GEN}	V
Pulse Voltage	V_{GEN}	0V to V_{DD}	V
Pulse Frequency Square Wave	f_{GEN}	$50k \leq f \leq 1M$ 50% Duty Cycle	Hz
Positive Supply Voltage (Input Side)	V_{CC}	V_{DD}	V
Positive Supply Voltage (Output Side)	V_{DD}	15 (+0 -0.5)	V
Negative Supply Voltage	V_{SS}	0	V

NOTES:

1. Input Protection Resistor = Output Load = 2k Ω min to 47k Ω max.

2.8 OPERATING LIFE CONDITIONS

The conditions shall be as specified for Power Burn-in.

APPENDIX 'A'
AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
<p>Deviations from Screening Tests - Chart F3</p>	<p>External Visual Inspection: The criteria applicable to chip-outs are those described in MIL-STD-883, Test Method 2009, Paras 3.3.6(b) and 3.3.7(a).</p> <p>High Temperature Reverse Bias Burn-in: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.</p> <p>Power Burn-in test is performed using STMicroelectronics Specification Ref: 0019255.</p> <p>Solderability is not applicable unless specifically stipulated in the Purchase Order.</p>
<p>Deviations from Qualification and Periodic Tests - Chart F4</p>	<p>External Visual Inspection: The criteria applicable to chip-outs are those described in MIL-STD-883, Test Method 2009, Paras 3.3.6(b) and 3.3.7(a).</p> <p>Operating Life: The temperature limits of MIL-STD-883, Para. 4.5.8(c) may be used.</p>
<p>Deviations from High and Low Temperatures Electrical Measurements</p>	<p>High and Low Temperatures Electrical Measurements may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes High and Low Temperatures Electrical Measurements per the Detail Specification.</p> <p>A summary of the pilot lot testing shall be provided if required by the Purchase Order.</p>
<p>Deviations from Room Temperature Electrical Measurements</p>	<p>All AC characteristics (Capacitance and Timings) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification.</p> <p>A summary of the pilot lot testing shall be provided if required by the Purchase Order.</p>